

# **FPN330** FPN330A



## **NPN Low Saturation Transistor**

These devices are designed for high current gain and low saturation voltage with collector currents up to 3.0 A continuous. Sourced from Process NB.

# **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	30	V	
V <sub>CBO</sub>	Collector-Base Voltage	50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V	
I <sub>C</sub>	Collector Current - Continuous	3.0	А	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FPN330 / FPN330A	
P <sub>D</sub>	Total Device Dissipation	1.0	W
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# **NPN Low Saturation Transistor**

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TA = 25°C unless otherwise noted

Symbol	Parameter	lest Conditions	WIIN	wax	Units
OFF CHA	RACTERISTICS				
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	30		V
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 100  \mu A,  I_E = 0$	50		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100  \mu A,  I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		100	nA
		$V_{CB} = 30 \text{ V}, I_{E} = 0, T_{A} = 100^{\circ}\text{C}$		10	μΑ
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		100	nA

### ON CHARACTERISTICS\*

h <sub>FE</sub>	DC Current Gain	$I_C = 100 \text{ mA}, V_{CE} = 2.0 \text{ V}$	330	100		
			330A	250		
		$I_C = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$		120		
		$I_C = 2.0 \text{ A}, V_{CE} = 2.0 \text{ V}$		50		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$	330		500	mV
- ( )			330A		450	mV
		$I_C = 2.0 \text{ A}, I_B = 200 \text{ mA}$			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$			1.25	V
V <sub>BE(on)</sub>	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$			1.0	V

### SMALL SIGNAL CHARACTERISTICS

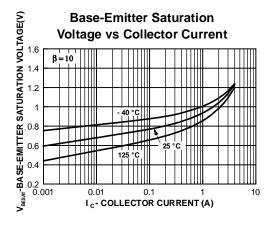
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		30	pF
F <sub>T</sub>	Transition Frequency	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 100  MHz	100		MHz

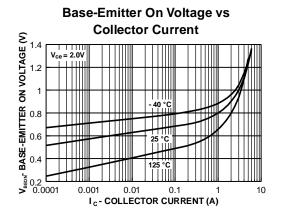
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

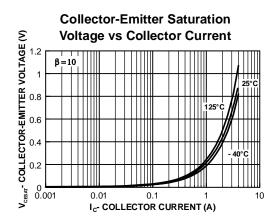
### **NPN Low Saturation Transistor**

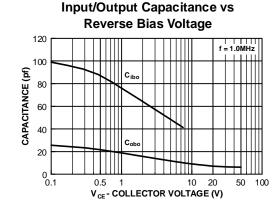
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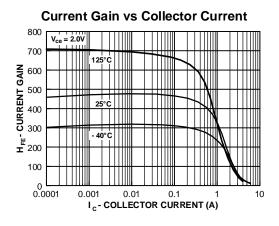
# **Typical Characteristics**

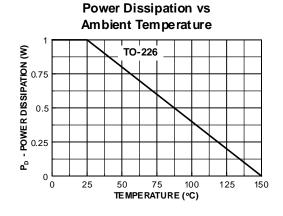


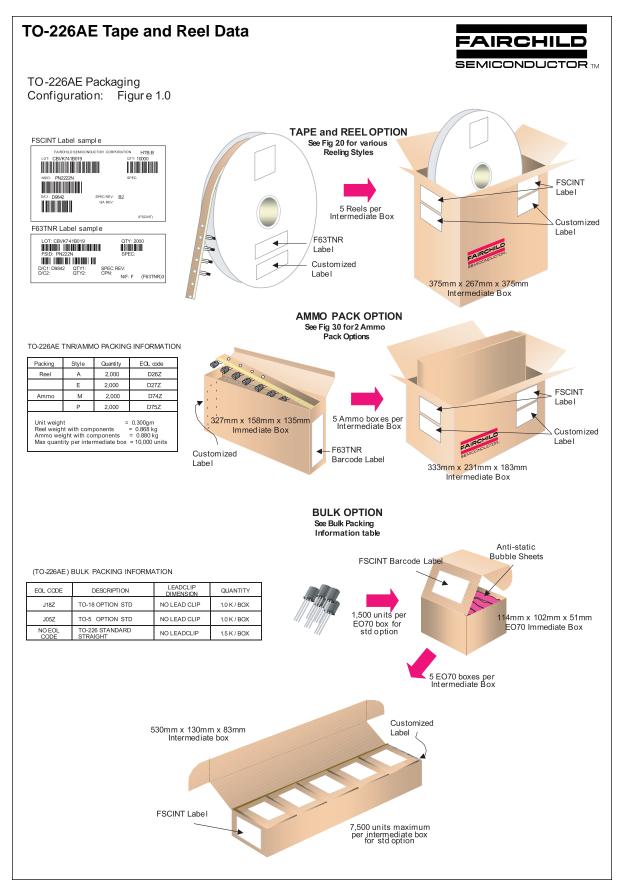








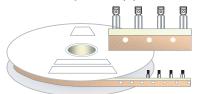




# **TO-226AE Tape and Reel Data, continued**

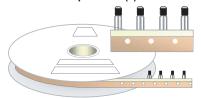
**TO-226AE Reeling Style Configuration:** Figure 2.0

Machine Option "A" (H)



Style "A" D26Z, D70Z (s/h)

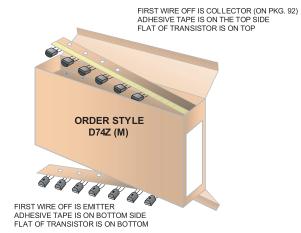
Machine Option "E"(J)



Style "E" D27Z, D71Z (s/h)

# TO-226AE Radial Ammo Packaging

**Configuration:** Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON BOTTOM



FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

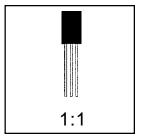
#### **TO-226AE Tape and Reel Data, continued** TO-226AE Tape and Reel Taping Dimension Configuration: Figure 4.0 ITEM DESCRIPTION SYMBOL DIMENSION Base of Package to Lead Bend 0.098 (max) Component Height Hb 1.078 (+/- 0.050) User Direction of Feed Lead Clinch Height 0.630 (+/- 0.020) HO Component Base Height H1 0.748 (+/- 0.020) Component Alignment (side/side) Pd 0.040 (max) Component Alignment (front/back) Hd 0.031 (max) Component Pitch 0.500 (+/- 0.020) РО Feed Hole Pitch 0.500 (+/- 0.008) Hole Center to First Lead P1 0.150 (+0.009, -0.010) Hole Center to Component Center P2 0.247 (+/- 0.007) Lead Spread F1/F2 0.104 (+/- 0 010) Lead Thickness d 0.018 (+0.002, -0.003) 0.429 (max) Cut Lead Length 0.209 (+0.051, -0.052) Taped Lead Length L1 Taped Lead Thickness 0.032 (+/- 0.006) Carrier Tape Thickness t1 0.021 (+/- 0.006) TO-226AE Reel 0.708 (+0.020, -0.019) Carrier Tape Width W Configuration: Figure 5.0 Hold - down Tape Width wo 0.236 (+/- 0.012) 0.035 (max) Hold - down Tape position W1 0.360 (+/- 0.025) Feed Hole Position W2 0.157 (+0.008, -0.007) DO Sprocket Hole Diameter Lead Spring Out S 0.004 (max) Note: All dmensions are in inches. D4 ITEM DESCRIPTION SYMBOL MINIMUM MAXIMUM Red Diameter 13975 14.025 Arbor Hole Diameter (Standard) 1.160 1.200 D2 D2 0.650 0.700 (Small Hole) Core Diameter D3 3.100 3.300 Hub Recess Inner Diameter 2.700 3.100 D4 Hub Recess Depth W 1 0.370 0.570 Range to Range Inner Width 1.630 Hub to Hub Center Width 2.090 Note: All dimensions are inches

# **TO-226AE Package Dimensions**



# TO-226AE (FS PKG Code 95, 99)

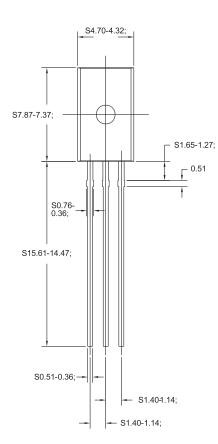


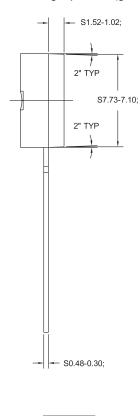


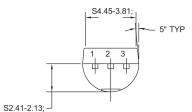
Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.300







	PIN	99	95		
	1	Е	Ε		
	2	В	С		
	3	С	В		
TO-226AE (95,99)					

For leadformed option ordering, refer to Tape & Reel data information.

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